

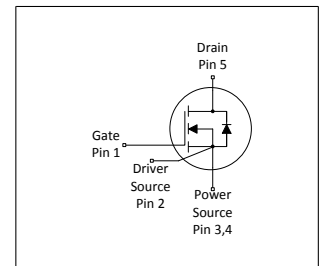
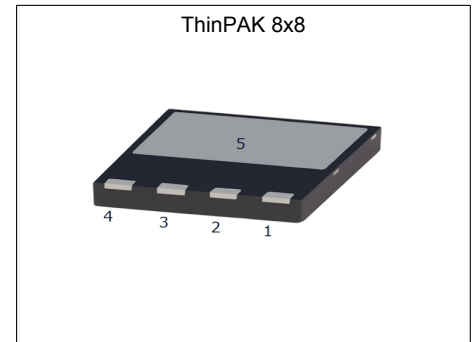
MOSFET

650V CoolMOS™ CFD2 Power Transistor

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. 650V CoolMOS™ CFD2 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The resulting devices provide all benefits of a fast switching SJ MOSFET while offering an extremely fast and robust body diode. This combination of extremely low switching, commutation and conduction losses together with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler.

ThinPAK

ThinPAK is a new leadless SMD package for HV MOSFETs. The new package has a very small footprint of only 64mm² (vs. 150mm² for the D²PAK) and a very low profile with only 1mm height (vs. 4.4mm for the D²PAK). The significantly smaller package size, combined with benchmark low parasitic inductances, provides designers with a new and effective way to decrease system solution size in power-density driven designs.



Features

- Reduced board space consumption
- Increased power density
- Short commutation loop
- Smooth switching waveform
- Ultra-fast body diode
- Very high commutation ruggedness
- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Easy to use/drive
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)
- Pb-free plating, Halogen free mold compound



Potential applications

650V CoolMOS™ CFD2 is especially suitable for resonant switching stages for e.g. PC Silverbox, LCD TV, Lighting, Server and Telecom.

Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{ds} @ T_{jmax}$	700	V
$R_{DS(on),max}$	0.165	Ω
$Q_{g,typ}$	86	nC
$I_{D,pulse}$	67	A
$E_{oss} @ 400V$	6.8	μJ
Body diode di_F/dt	900	A/ μs
Q_{rr}	0.7	μC
t_r	140	ns
I_{rrm}	8.8	A

Type / Ordering Code	Package	Marking	Related Links
IPL65R165CFD	PG-VSON-4	65F6165	see Appendix A

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1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	21.3 13.5	A	$T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	67	A	$T_C = 25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	614	mJ	$I_D = 4.3\text{ A}$; $V_{DD} = 50\text{ V}$
Avalanche energy, repetitive	E_{AR}	-	-	0.93	mJ	$I_D = 4.3\text{ A}$; $V_{DD} = 50\text{ V}$
Avalanche current, repetitive	I_{AR}	-	-	4.3	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS} = 0 \dots 400\text{ V}$
Gate source voltage	V_{GS}	-20 -30	-	20 30	V	static; AC ($f > 1\text{ Hz}$)
Power dissipation	P_{tot}	-	-	195	W	$T_C = 25^\circ\text{C}$
Operating and storage temperature	T_j, T_{stg}	-40	-	150	$^\circ\text{C}$	-
Continuous diode forward current	I_S	-	-	21.3	A	$T_C = 25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	67	A	$T_C = 25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	50	V/ns	$V_{DS} = 0 \dots 400\text{ V}$, $I_{SD} \leq I_D$, $T_j = 25^\circ\text{C}$ see table 8
Maximum diode commutation speed	di _f /dt	-	-	900	A/ μs	$V_{DS} = 0 \dots 400\text{ V}$, $I_{SD} \leq I_D$, $T_j = 25^\circ\text{C}$ see table 8

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.64	$^\circ\text{C/W}$	-
Thermal resistance, junction - ambient ⁴⁾	R_{thJA}	-	-	62 45	$^\circ\text{C/W}$	SMD version, device on PCB, minimal footprint SMD version, device on PCB, 6cm ² cooling area
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	$^\circ\text{C}$	reflow MSL2a

¹⁾ Limited by $T_{j,max}$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

⁴⁾ Device on 40mm*40mm*1.5mm one layer epoxy PCB FR4 with 6cm² copper area (thickness 70 μm) for drain connection. PCB is vertical without air steam cooling.

3 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{(GS)th}$	3.5	4	4.5	V	$V_{DS}=V_{GS}$, $I_D=0.9\text{ mA}$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=650\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ }^\circ\text{C}$ $V_{DS}=650\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=150\text{ }^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.149	0.165	Ω	$V_{GS}=10\text{ V}$, $I_D=9.3\text{ A}$, $T_j=25\text{ }^\circ\text{C}$ $V_{GS}=10\text{ V}$, $I_D=9.3\text{ A}$, $T_j=150\text{ }^\circ\text{C}$
Gate resistance	R_G	-	1.5	-	Ω	$f=1\text{ MHz}$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	2340	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	110	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=100\text{ V}$, $f=1\text{ MHz}$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	90	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=0\dots400\text{ V}$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	420	-	pF	$I_D=\text{constant}$, $V_{GS}=0\text{ V}$, $V_{DS}=0\dots400\text{ V}$
Turn-on delay time	$t_{d(on)}$	-	12.4	-	ns	$V_{DD}=400\text{ V}$, $V_{GS}=13\text{ V}$, $I_D=14\text{ A}$, $R_G=1.8\Omega$; see table 9
Rise time	t_r	-	7.6	-	ns	$V_{DD}=400\text{ V}$, $V_{GS}=13\text{ V}$, $I_D=14\text{ A}$, $R_G=1.8\Omega$; see table 9
Turn-off delay time	$t_{d(off)}$	-	52.8	-	ns	$V_{DD}=400\text{ V}$, $V_{GS}=13\text{ V}$, $I_D=14\text{ A}$, $R_G=1.8\Omega$; see table 9
Fall time	t_f	-	5.6	-	ns	$V_{DD}=400\text{ V}$, $V_{GS}=13\text{ V}$, $I_D=14\text{ A}$, $R_G=1.8\Omega$; see table 9

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	15	-	nC	$V_{DD}=480\text{ V}$, $I_D=14\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	Q_{gd}	-	47	-	nC	$V_{DD}=480\text{ V}$, $I_D=14\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	Q_g	-	86	-	nC	$V_{DD}=480\text{ V}$, $I_D=14\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	6.4	-	V	$V_{DD}=480\text{ V}$, $I_D=14\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$

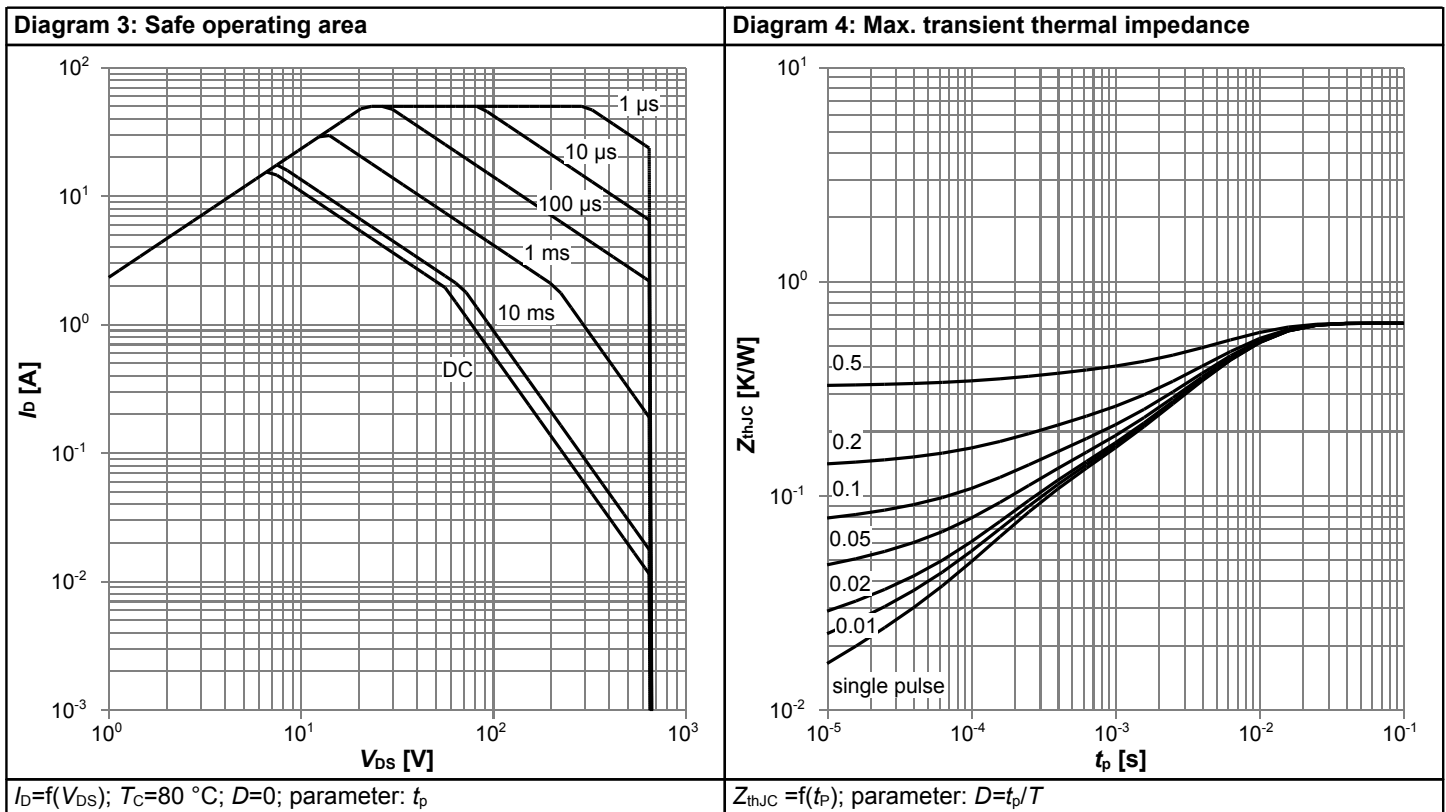
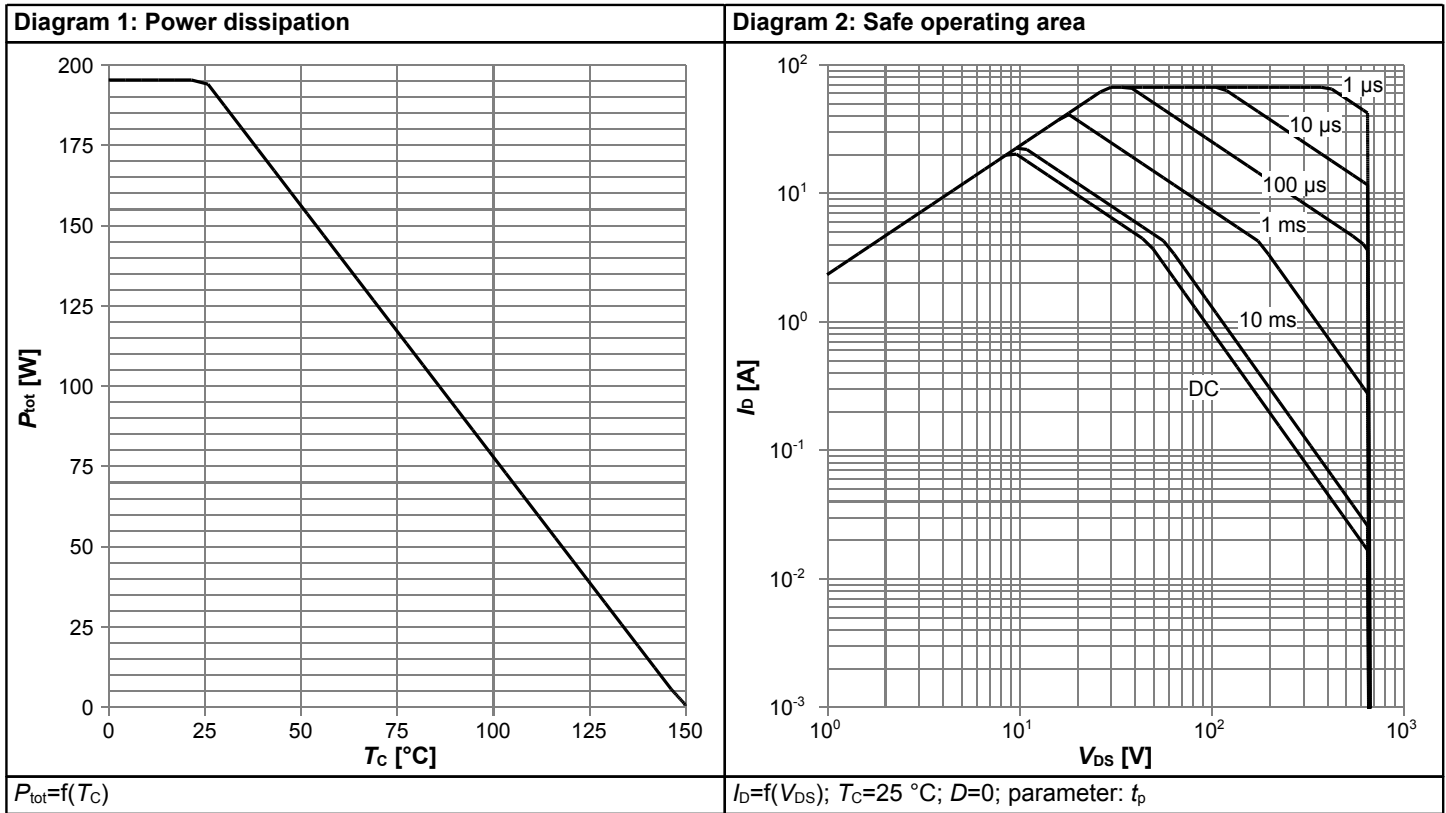
¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0\text{ V}$, $I_F=14\text{ A}$, $T_j=25\text{ °C}$
Reverse recovery time	t_{rr}	-	140	-	ns	$V_R=400\text{ V}$, $I_F=14\text{ A}$ $di_F/dt=100\text{ A}/\mu\text{s}$ see table 8
Reverse recovery charge	Q_{rr}	-	0.7	-	μC	$V_R=400\text{ V}$, $I_F=14\text{ A}$ $di_F/dt=100\text{ A}/\mu\text{s}$ see table 8
Peak reverse recovery current	I_{rrm}	-	8.8	-	A	$V_R=400\text{ V}$, $I_F=14\text{ A}$ $di_F/dt=100\text{ A}/\mu\text{s}$ see table 8

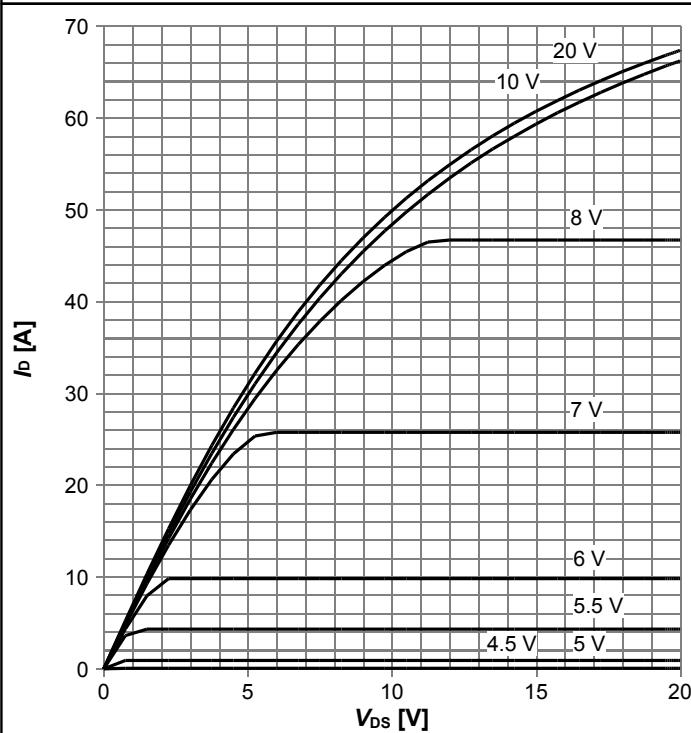
4 Electrical characteristics diagrams



650V CoolMOS™ CFD2 Power Transistor

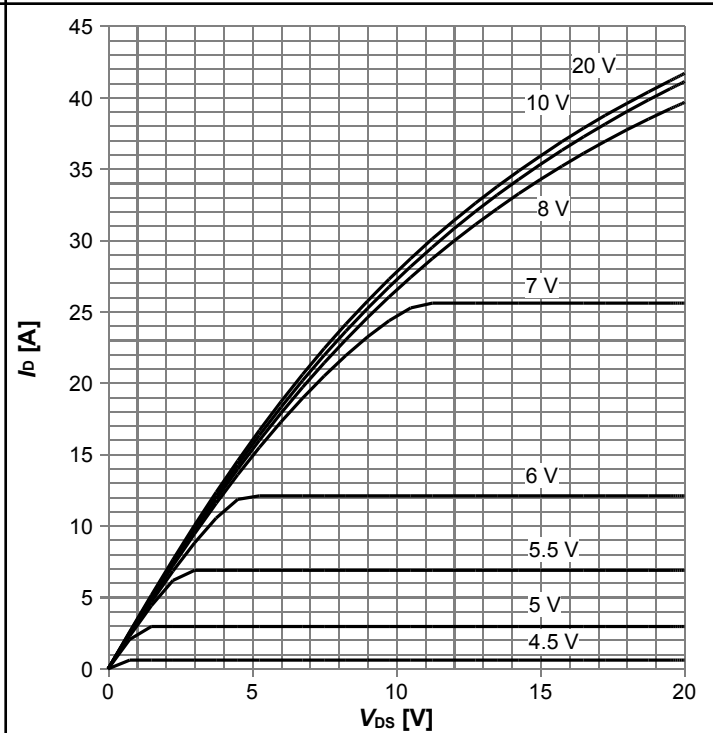
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Diagram 5: Typ. output characteristics



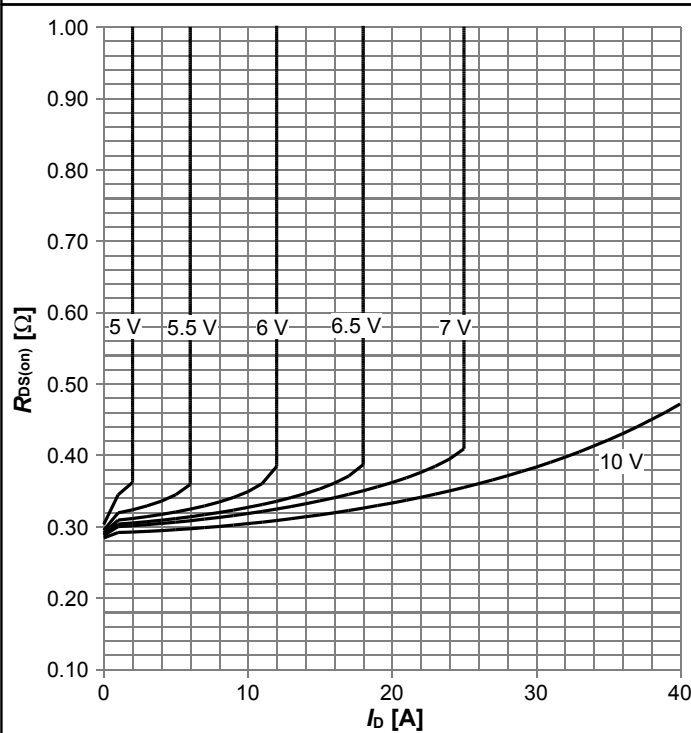
$I_D=f(V_{DS}); T_j=25\text{ °C};$ parameter: V_{GS}

Diagram 6: Typ. output characteristics



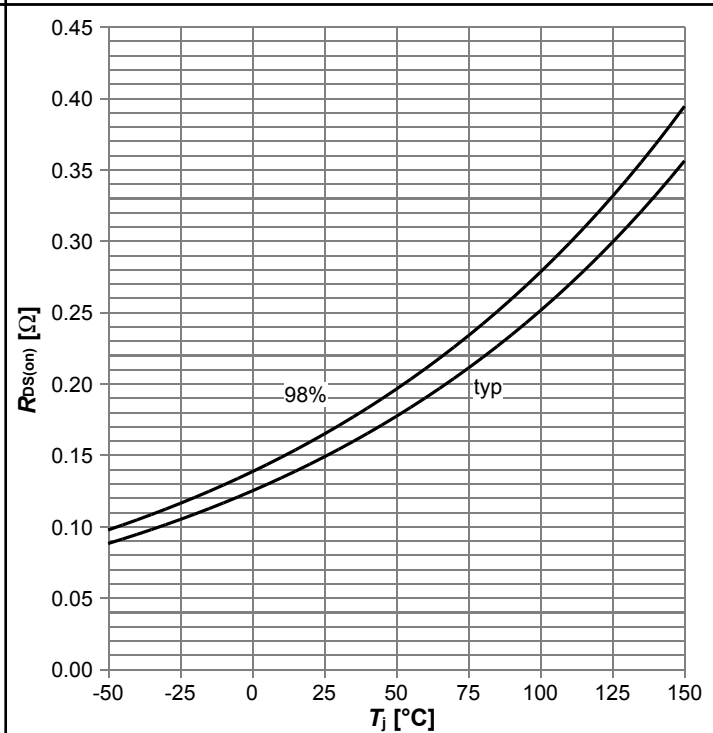
$I_D=f(V_{DS}); T_j=125\text{ °C};$ parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



$R_{DS(on)}=f(I_D); T_j=125\text{ °C};$ parameter: V_{GS}

Diagram 8: Drain-source on-state resistance

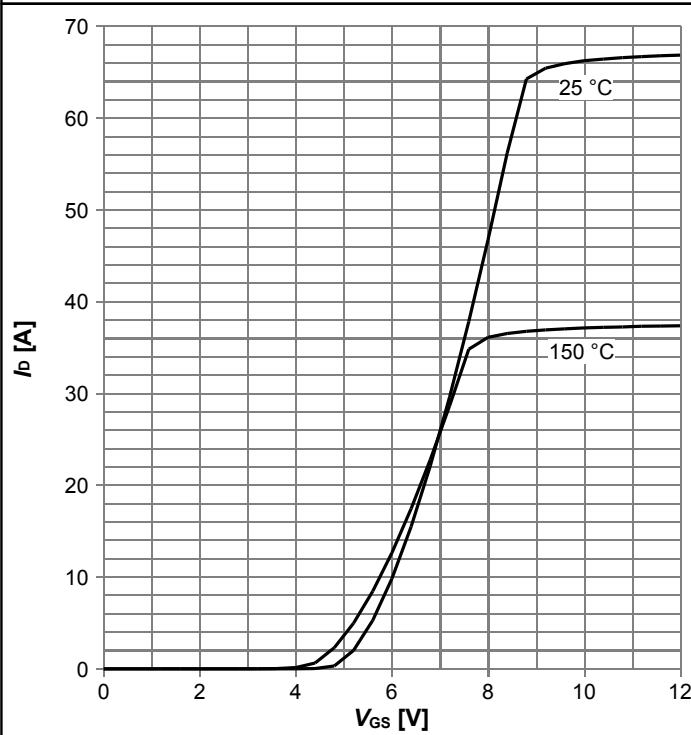


$R_{DS(on)}=f(T_j); I_D=9.3\text{ A}; V_{GS}=10\text{ V}$

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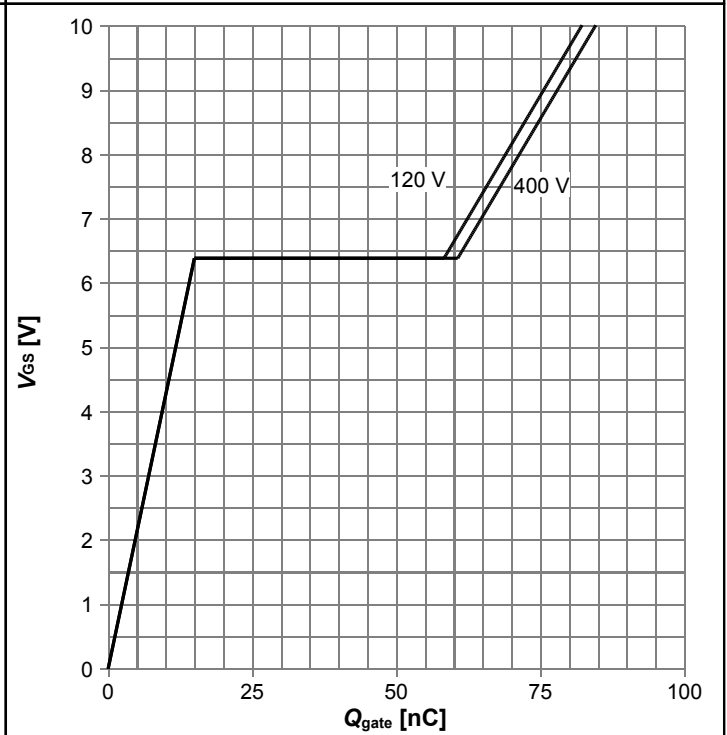
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Diagram 9: Typ. transfer characteristics



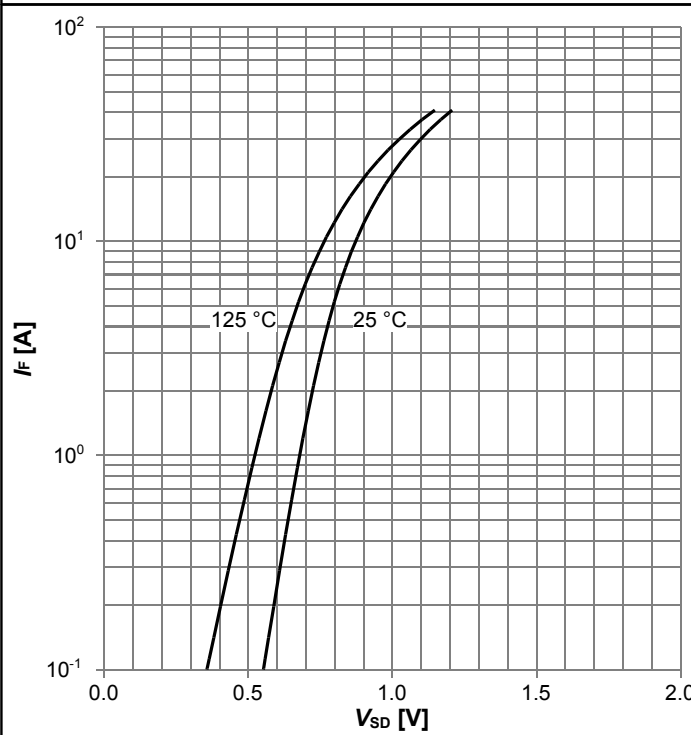
$I_D = f(V_{GS}); V_{DS} = 20V; \text{parameter: } T_j$

Diagram 10: Typ. gate charge



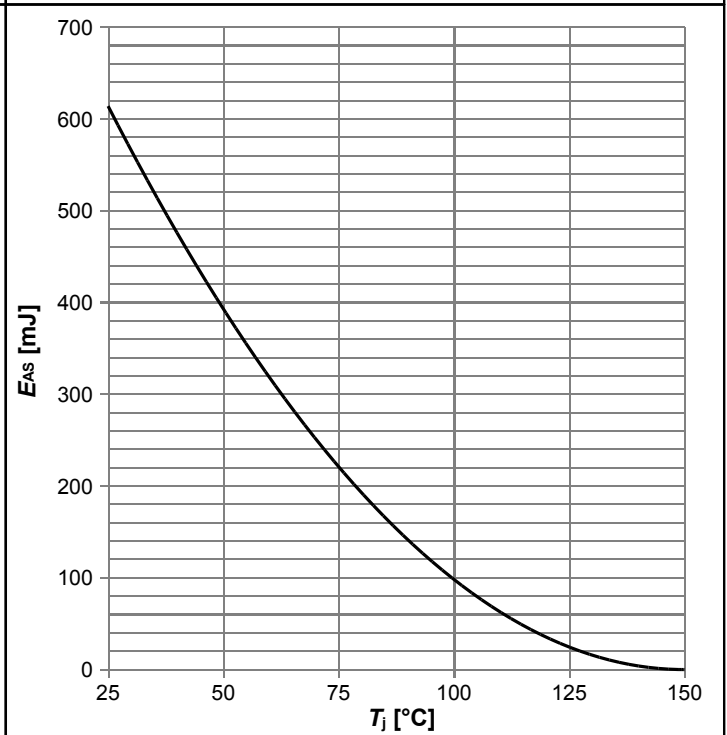
$V_{GS} = f(Q_{gate}); I_D = 14 \text{ A pulsed}; \text{parameter: } V_{DD}$

Diagram 11: Forward characteristics of reverse diode



$I_F = f(V_{SD}); \text{parameter: } T_j$

Diagram 12: Avalanche energy

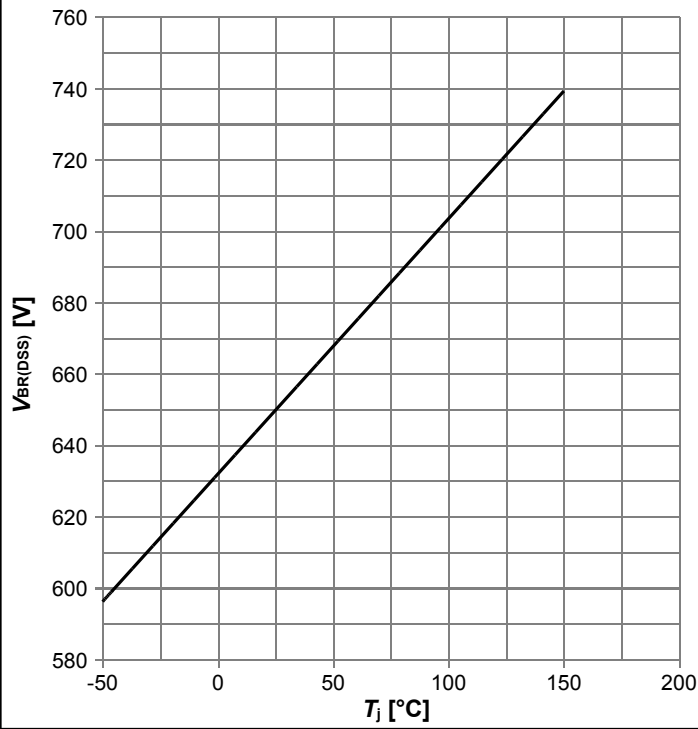


$E_{AS} = f(T_j); I_D = 4.3 \text{ A}; V_{DD} = 50 \text{ V}$

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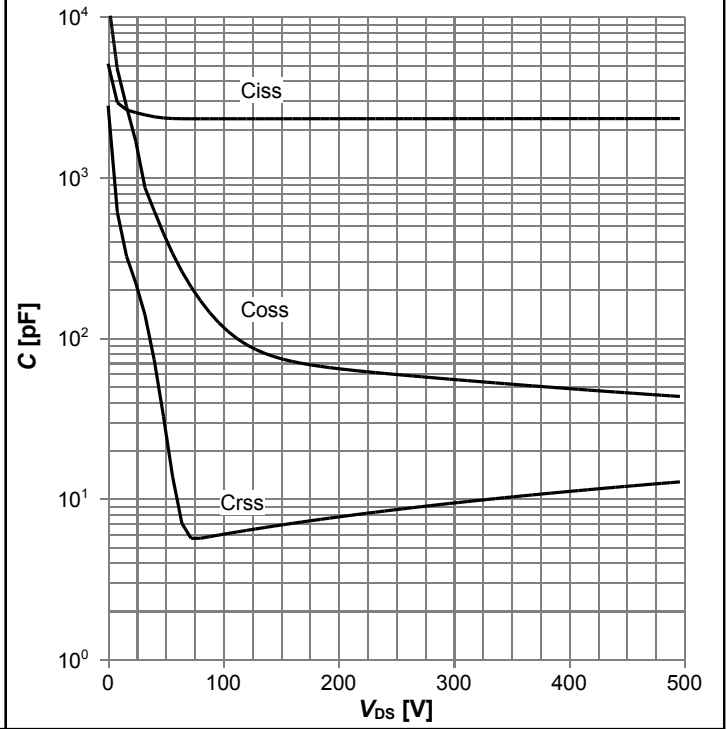
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Diagram 13: Drain-source breakdown voltage



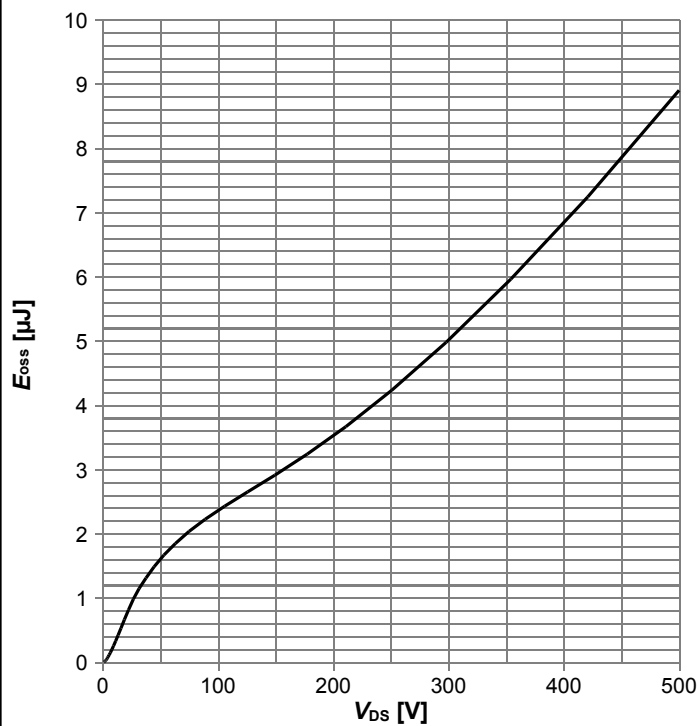
$V_{BR(DSS)}=f(T_j); I_D=1\text{ mA}$

Diagram 14: Typ. capacitances



$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$

Diagram 15: Typ. Coss stored energy



$E_{oss}=f(V_{DS})$

5 Test Circuits

Table 8 Diode characteristics

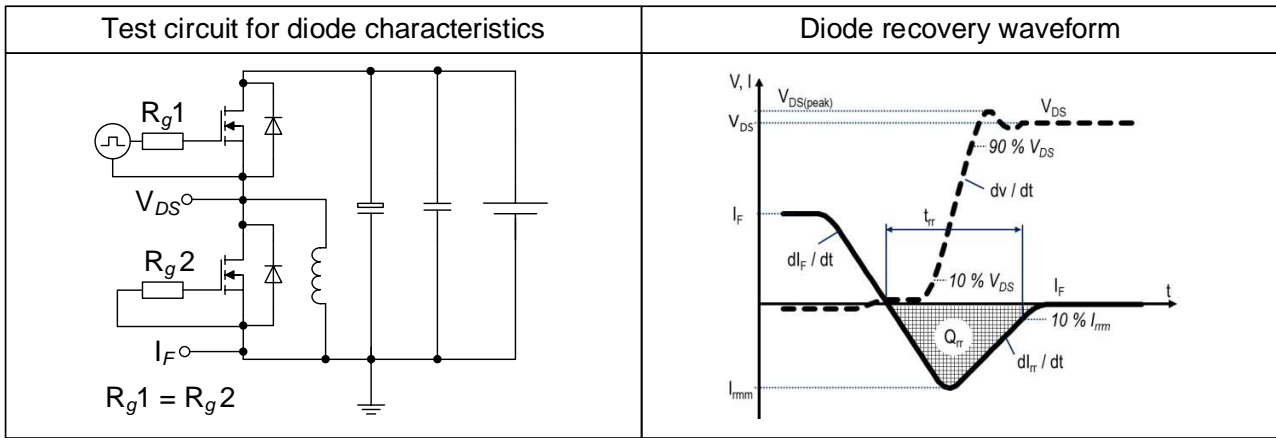


Table 9 switching times (ss)

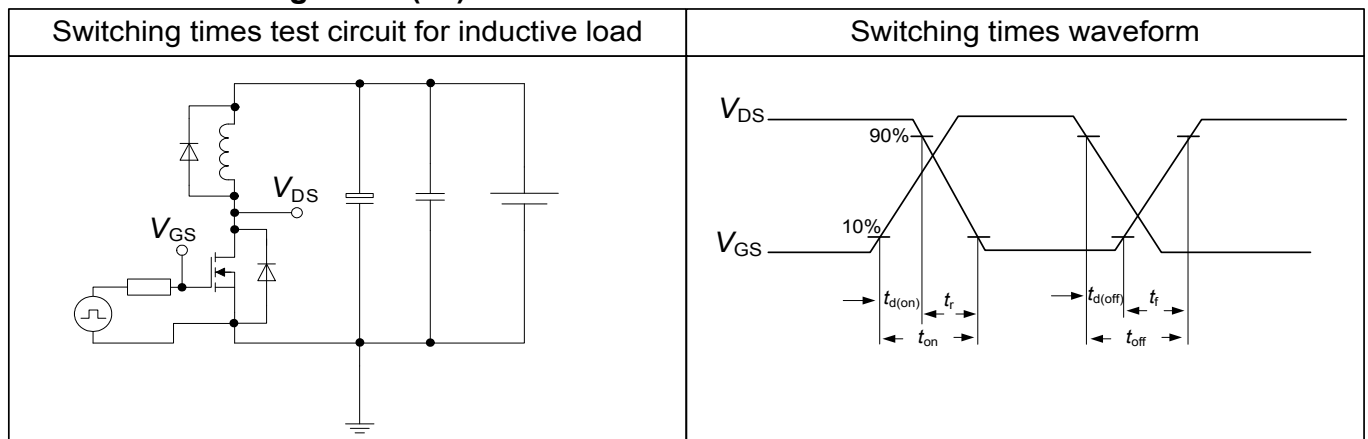
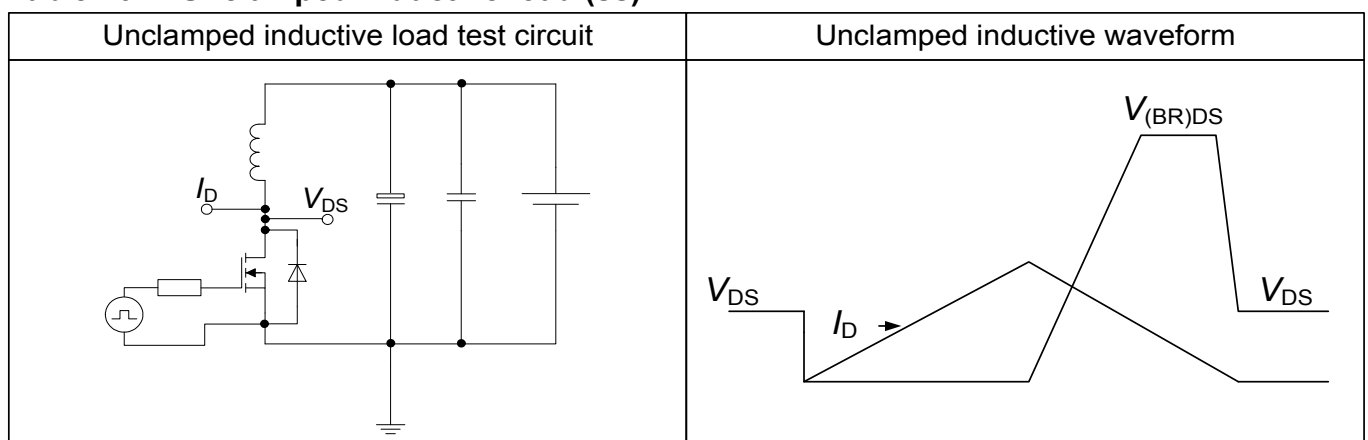


Table 10 Unclamped inductive load (ss)



6 Package Outlines

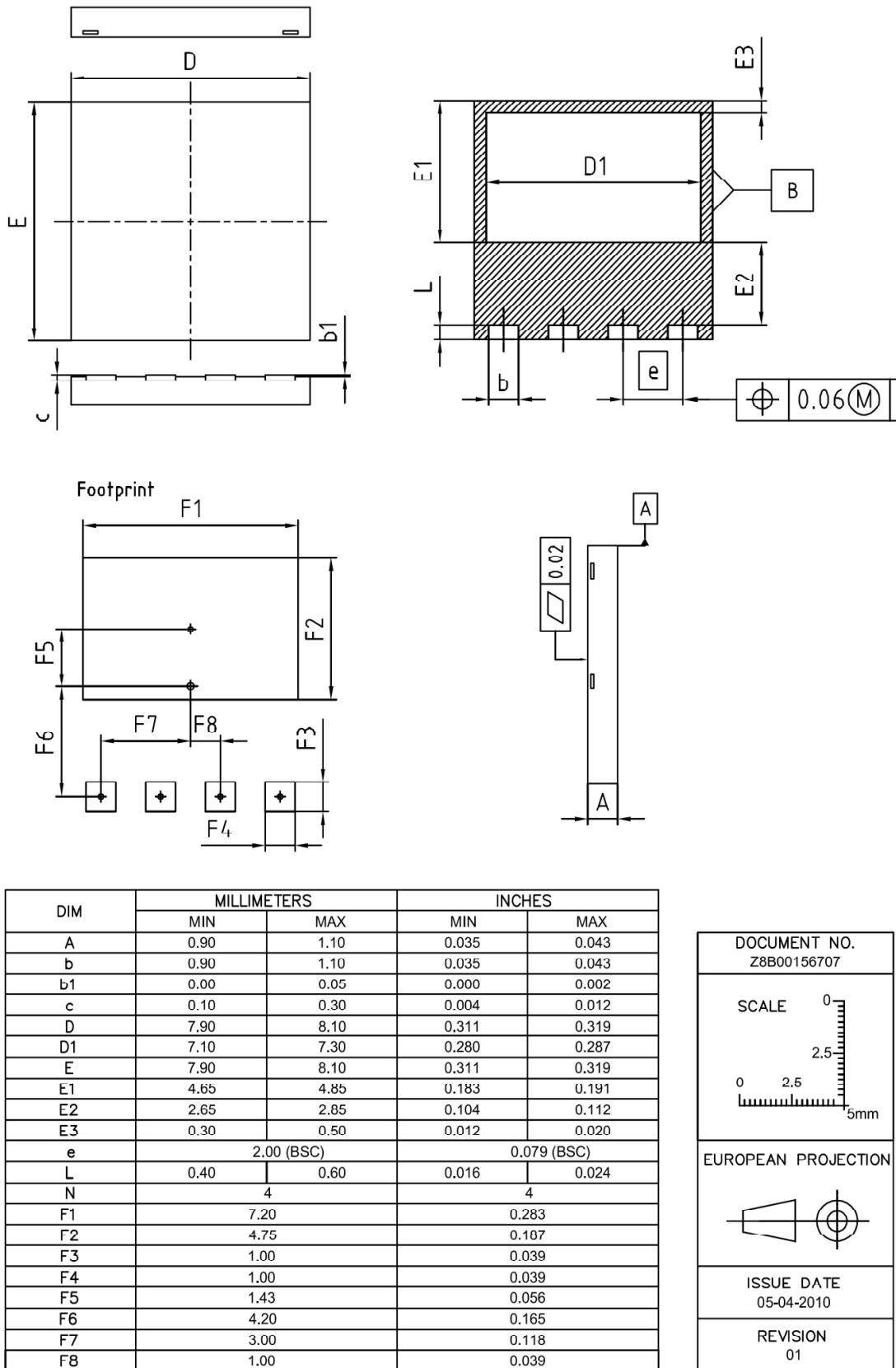


Figure 1 Outline PG-VSON-4, dimensions in mm/inches

7 Appendix A

Table 11 Related Links

- IFX CoolMOS Webpage: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPL65R165CFD

Revision: 2017-09-07, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2014-03-19	Release of final version
2.1	2017-09-07	Updated MSL; style updated

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